



**THE DATASHEET OF
ZXM62N03GTA**



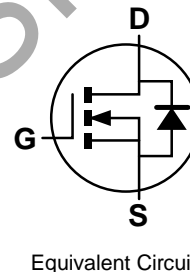
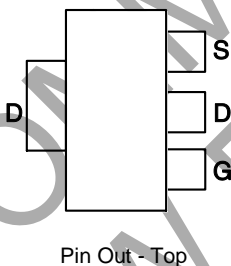
Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D $T_A = +25^\circ C$
30V	$0.11\Omega @ V_{GS} = 10V$	4.7A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Audio Output Stage
- Relay and Solenoid Driving
- Motor Control



Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

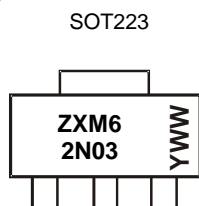
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe.
Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.112 grams (Approximate)

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXM62N03GTA	ZXM62N03	7	12	1,000
ZXM62N03GTC	ZXM62N03	13	12	4,000

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



ZXM62N03 = Product Type Marking Code
 YWW = Date Code Marking
 Y or \bar{Y} = Last Digit of Year (ex: 5 = 2015)
 WW or $\bar{W}W$ = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (V _{GS} = 10V, T _A = +25°C) (Note 6)	I _D	4.7	A
(V _{GS} = 10V, T _A = +70°C) (Note 6)		3.8	
(V _{GS} = 10V, T _A = +25°C) (Note 5)		3.4	
Pulsed Drain Current (Note 7)	I _{DM}	16	A
Continuous Source Current (Body Diode) (Note 6)	I _S	2.6	A
Pulsed Source Current (Body Diode) (Note 7)	I _{SM}	16	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25°C (Note 5)	P _D	2.0	W
Linear Derating Factor		16	mW/°C
Power Dissipation at T _A = +25°C (Note 6)	P _D	3.9	W
Linear Derating Factor		31	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	62.5	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	32	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

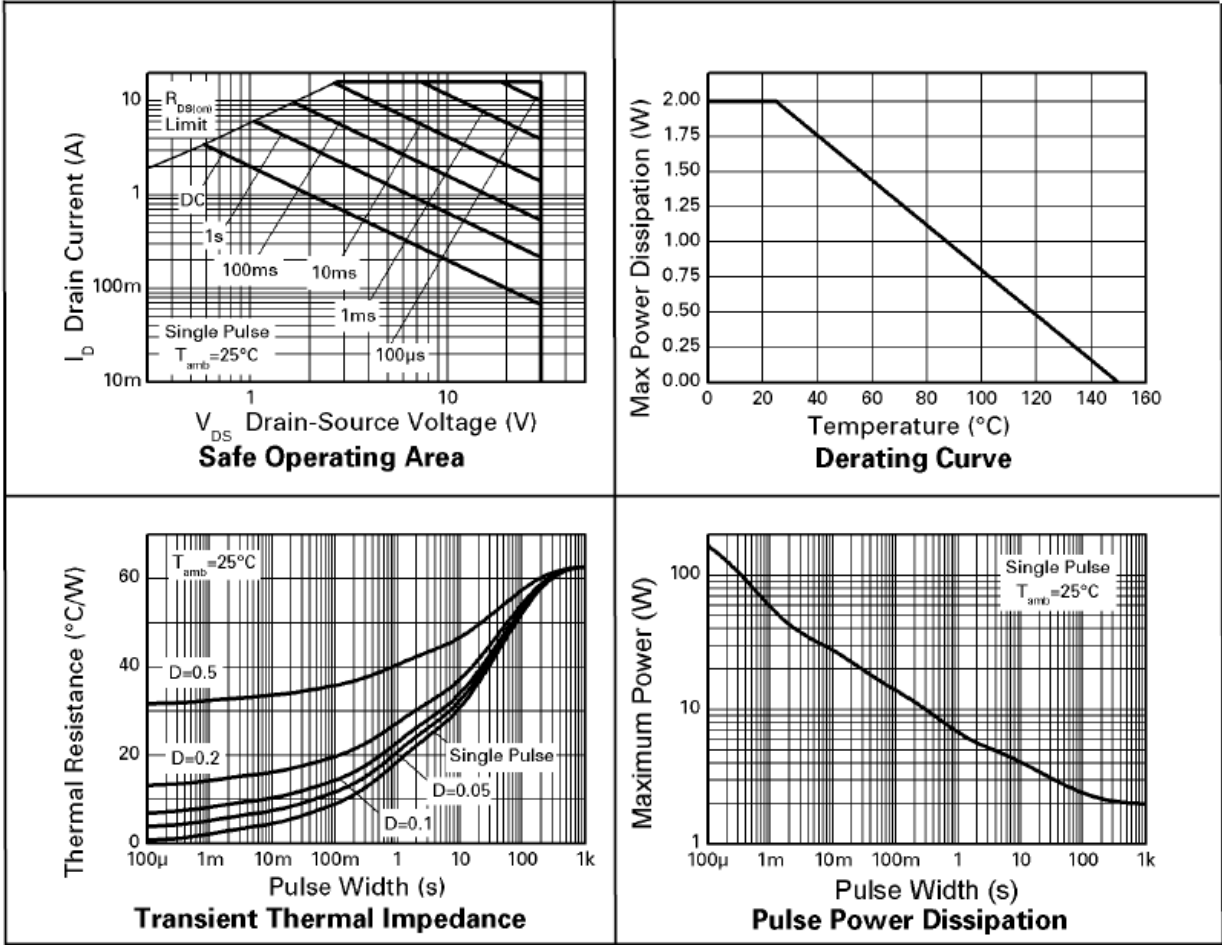
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	1	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}	—	—	0.11 0.15	Ω	V _{GS} = 10V, I _D = 2.2A V _{GS} = 4.5V, I _D = 1.1A
Forward Transconductance (Notes 8 & 10)	g _{fs}	1.1	—	—	S	V _{DS} = 15V, I _D = 1.1A
Diode Forward Voltage (Note 8)	V _{SD}	—	—	0.95	V	T _J = +25°C, I _S = 2.2A, V _{GS} = 0V
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	380	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	90	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	30	—	pF	
Turn-On Delay Time (Note 9)	t _{D(ON)}	—	2.9	—	ns	V _{DD} = 15V, I _D = 2.2A, V _{GS} = 10V, R _{GS} = 6Ω
Turn-On Rise Time (Note 9)	t _R	—	5.6	—	ns	
Turn-Off Delay Time (Note 9)	t _{D(OFF)}	—	11.7	—	ns	
Turn-Off Fall Time (Note 9)	t _F	—	6.4	—	ns	
Total Gate Charge (Note 9)	Q _g	—	—	9.6	nC	V _{DS} = 24V, V _{GS} = 10V, I _D = 2.2A
Gate-Source Charge (Note 9)	Q _{gs}	—	—	1.7	nC	
Gate-Drain Charge (Note 9)	Q _{gd}	—	—	2.8	nC	
Reverse Recovery Time	t _{RR}	—	18.8	—	ns	T _J = +25°C, I _F = 2.2A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	11.4	—	nC	

- Notes:
5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 6. For a device surface mounted on FR-4 PCB measured at t ≤ 10 seconds.
 7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05 pulse width limited by maximum junction temperature.
 8. Measured under pulsed conditions. Width = 300μs. Duty cycle ≤ 2%.
 9. Switching characteristics are independent of operating junction temperature.
 10. For design aid only, not subject to production testing.

NOT RECOMMENDED FOR NEW DESIGN
USE DMN3032LE and ZXMN6A11G



ZXM62N03G



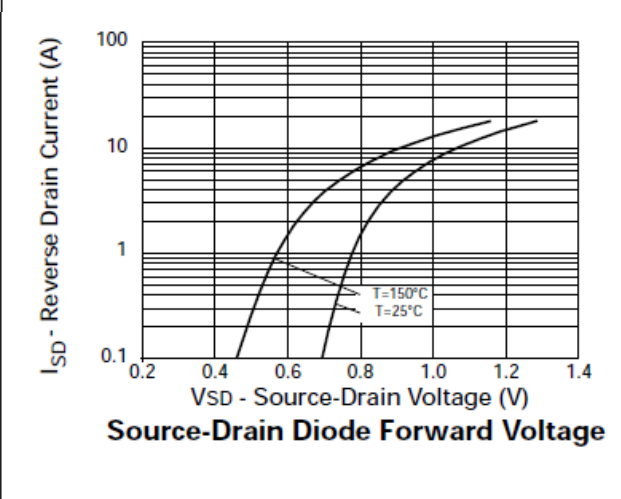
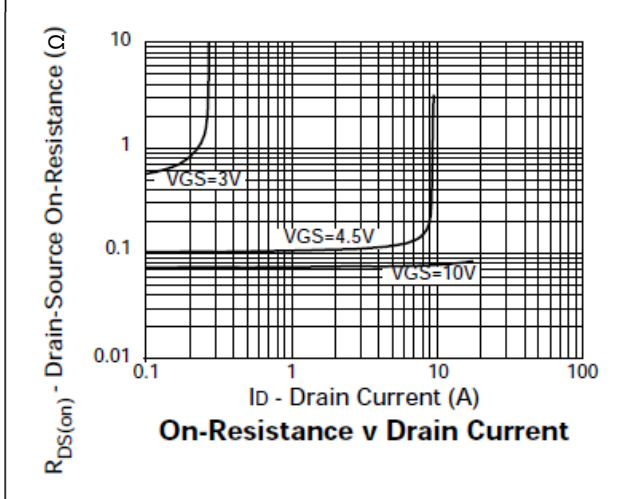
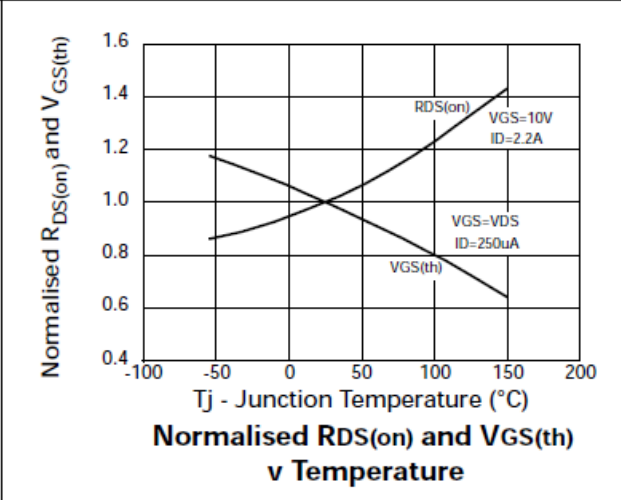
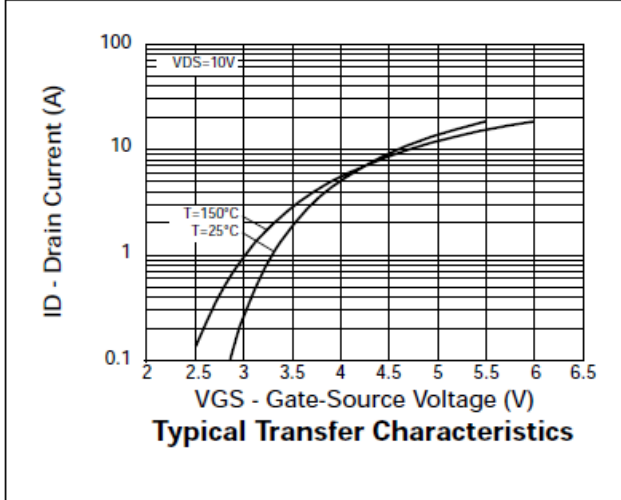
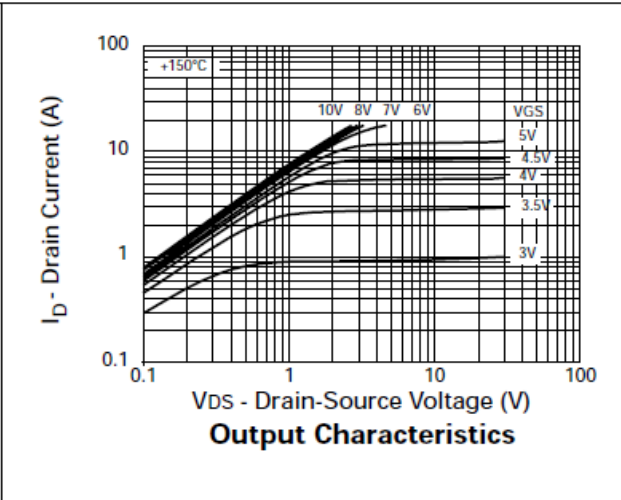
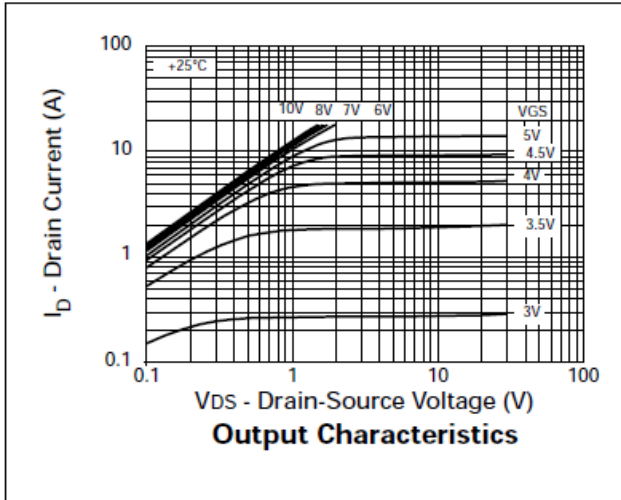
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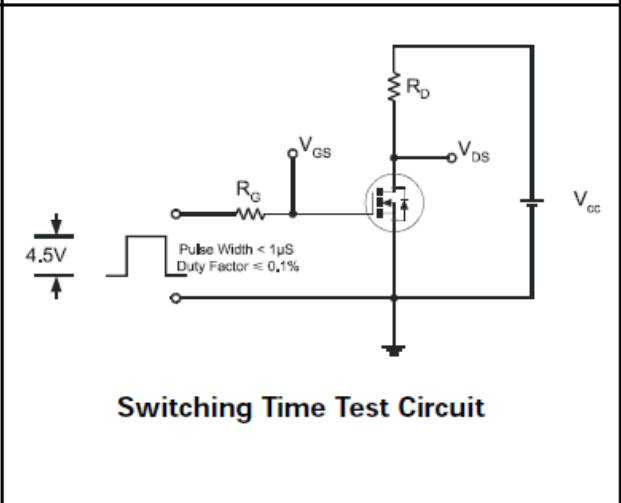
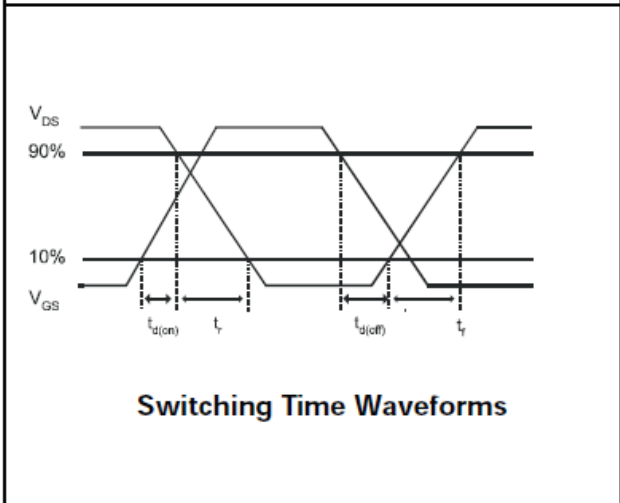
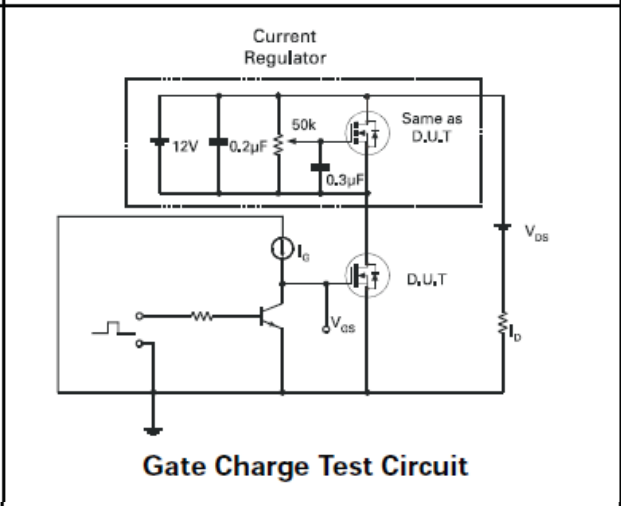
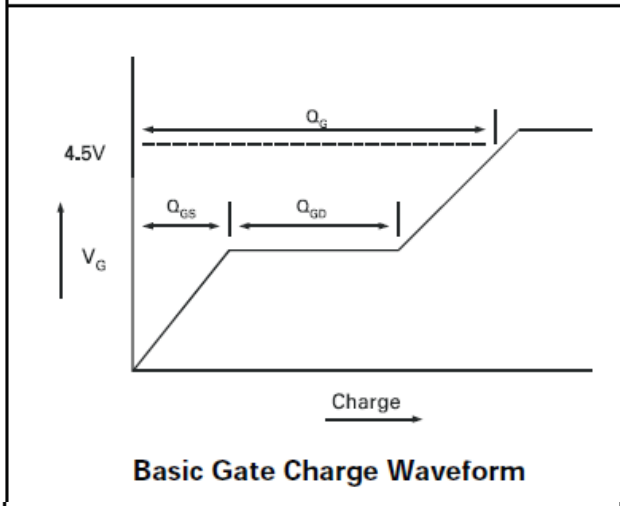
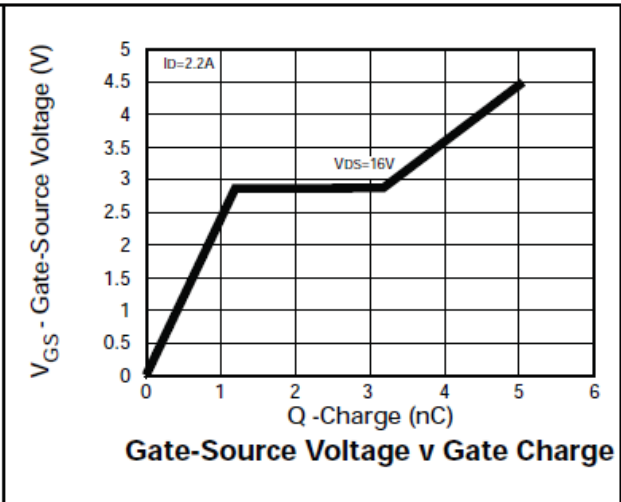
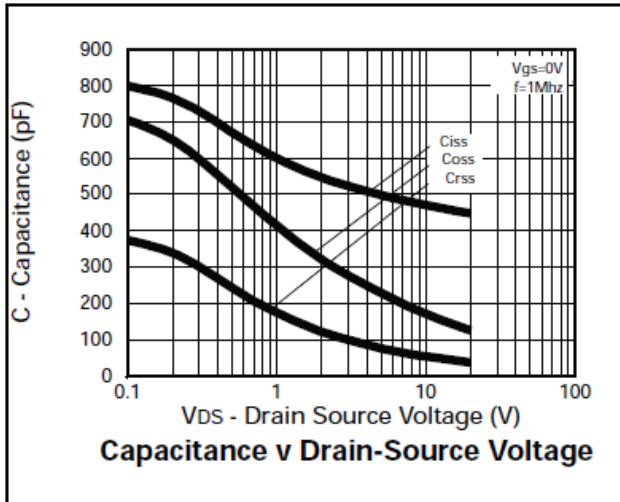


ZXM62N03G

Typical Characteristics



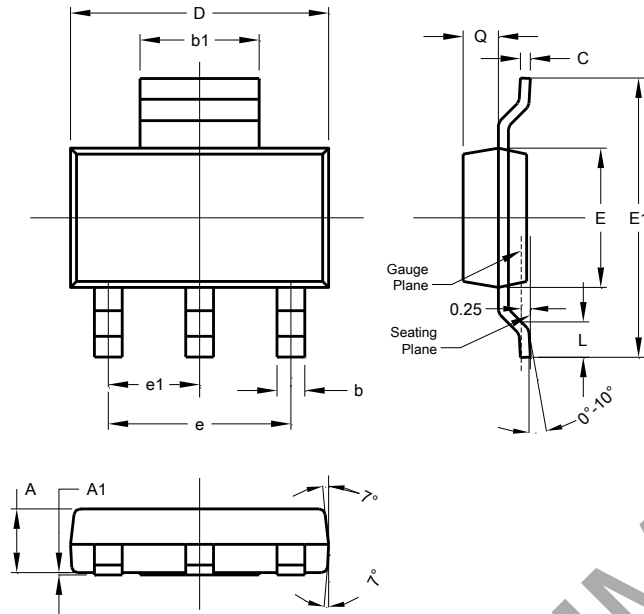
Typical Characteristics (Cont.)



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223

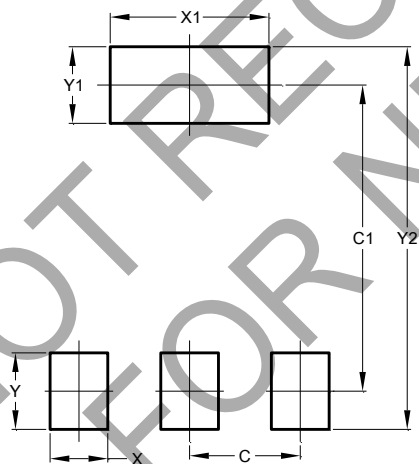


SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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